

Dual N-Channel Enhancement Mode Power MOSFET

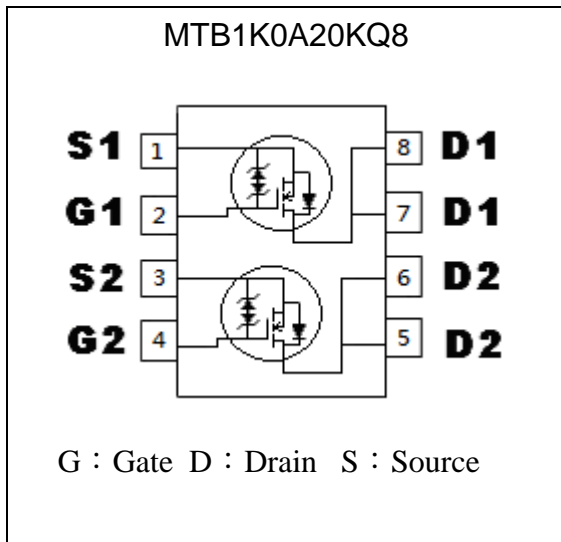
MTB1K0A20KQ8

BV_{DSS}	200V
I_D@V_{GS}=10V, T_A=25°C	0.9A
I_D@V_{GS}=10V, T_A=70°C	0.72A
R_{DS(on)}@V_{GS}=10V, I_D=1A	755mΩ (typ)
R_{DS(on)}@V_{GS}=4.5V, I_D=1A	785mΩ (typ)

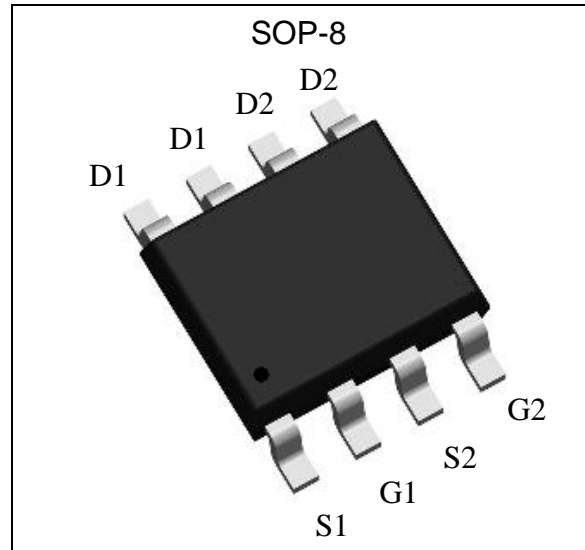
Features

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Dual N-ch MOSFET package
- ESD protected gate
- Pb-free lead plating & Halogen-free package

Equivalent Circuit

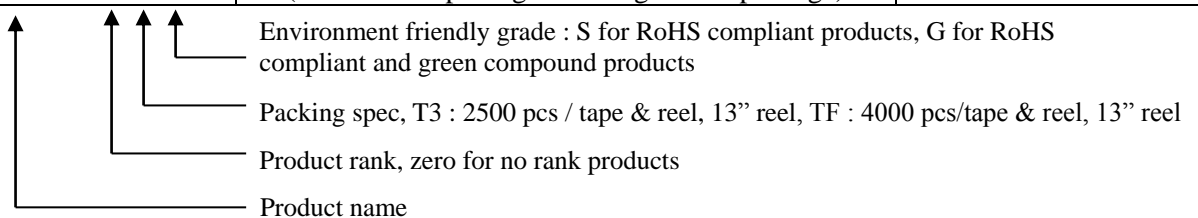


Outline



Ordering Information

Device	Package	Shipping
MTB1KA20KQ8-0-T3-G	SOP-8 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel
MTB1KA20KQ8-0-TF-G	SOP-8 (Pb-free lead plating and halogen-free package)	4000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	200	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current @ V _{GS} =10V, T _C =25°C	I _D	1.4	A
Continuous Drain Current @ V _{GS} =10V, T _C =100°C		0.89	
Continuous Drain Current @ V _{GS} =10V, T _A =25°C		0.9 (Note 2)	
Continuous Drain Current @ V _{GS} =10V, T _A =70°C		0.72 (Note 2)	
Pulsed Drain Current	I _{DM}	6 (Note 1)	
Avalanche Current @ L=0.1mH	I _{AS}	2	
Avalanche Energy @ L=1mH, I _D =2A, V _{DD} =50V	E _{AS}	2 (Note 4)	mJ
Power Dissipation for Dual Operation	P _D	2	W
Power Dissipation for Single Operation		1.6 (Note 2)	
		0.9 (Note 3)	
Operating Junction and Storage Temperature Range	T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	25	°C/W
Thermal Resistance, Junction-to-ambient, max, dual	R _{θJA}	62.5	
Thermal Resistance, Junction-to-ambient, max , single operation		78 (Note 2)	
		135 (Note 3)	

- Note : 1. Pulse width limited by maximum junction temperature
 2. Surface mounted on 1 in² copper pad of FR-4 board, pulse width≤10s.
 3. Surface mounted on minimum copper pad, pulse width≤10s.

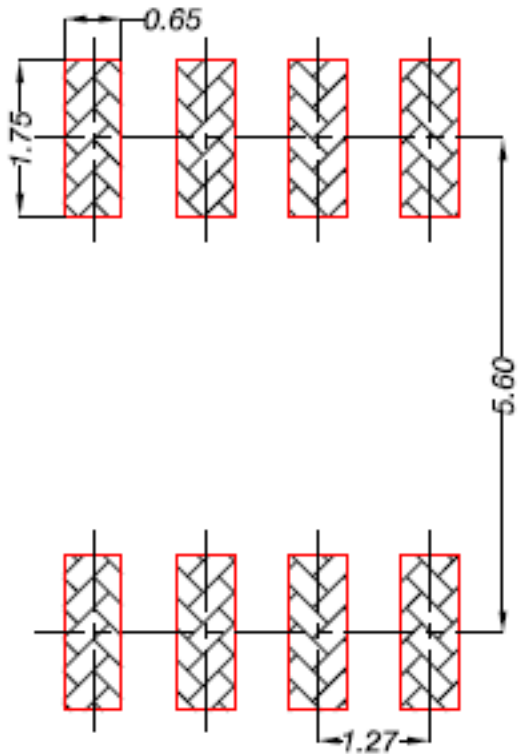
Characteristics (T_J=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	200	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	1	-	2.5		V _{DS} = V _{GS} , I _D =250μA
G _{FS} *1	-	3	-	S	V _{DS} = 10V, I _D =1A
I _{GSS}	-	-	±10	μA	V _{GS} =±16V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} = 160V, V _{GS} = 0V
	-	-	25		V _{DS} = 160V, V _{GS} = 0V, T _J =70°C
R _{DS(ON)} *1	-	0.755	2	Ω	V _{GS} = 10V, I _D =1A
	-	0.785	3		V _{GS} = 4.5V, I _D =1A
Dynamic					
Q _g *1, 2	-	8.5	12.8	nC	V _{DS} =160V, I _D =1A, V _{GS} =10V
Q _{gs} *1, 2	-	1.1	-		
Q _{gd} *1, 2	-	2.9	-		

$t_{d(ON)}$ *1, 2	-	16.4	24.6	ns	$V_{DS}=100V, I_D=2A, V_{GS}=10V, R_G=1\Omega$
t_r *1, 2	-	27	40.5		
$t_{d(OFF)}$ *1, 2	-	101	152		
t_f *1, 2	-	72	108		
C_{iss}	-	277	415	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
C_{oss}	-	15	22.5		
C_{rss}	-	8.7	13.1		
Source-Drain Diode					
I_S *1	-	-	0.9	A	
I_{SM} *3	-	-	6		
V_{SD} *1	-	0.79	1	V	$I_S=1A, V_{GS}=0V$
t_{rr} *1	-	32	-	ns	$I_F=1A, dI_F/dt=100A/\mu s$
Q_{rr} *1	-	35	-	nC	

Note : *1.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

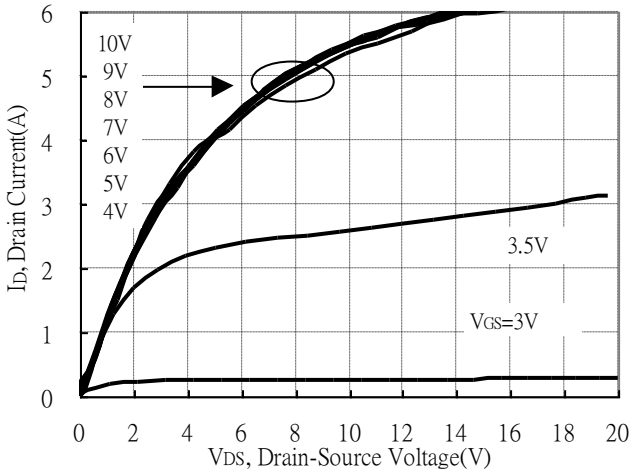
Recommended Soldering Footprint



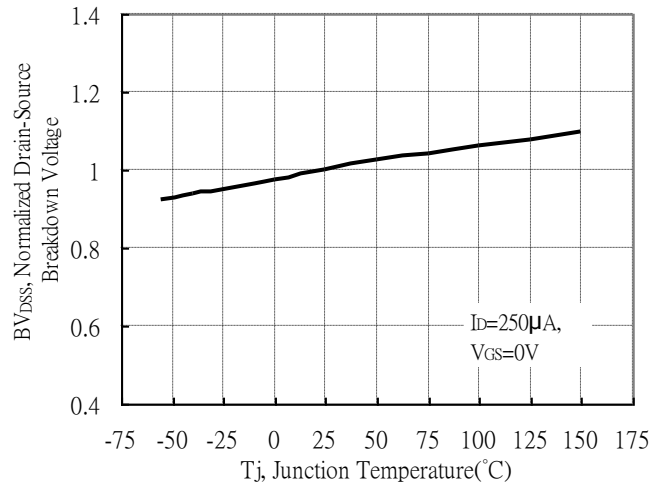


Typical Characteristics

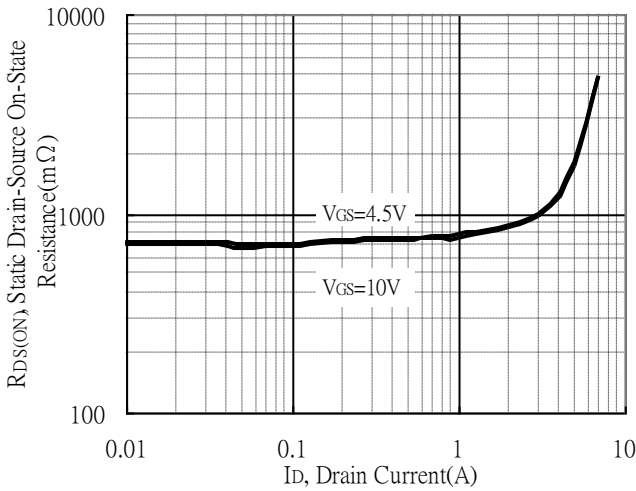
Typical Output Characteristics



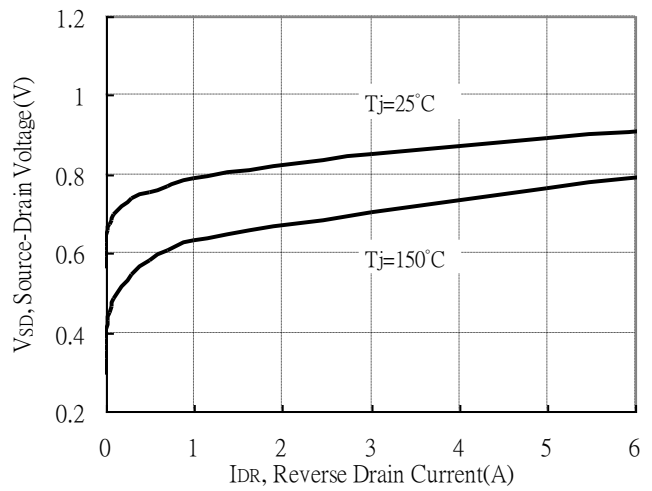
Brekdown Voltage vs Ambient Temperature



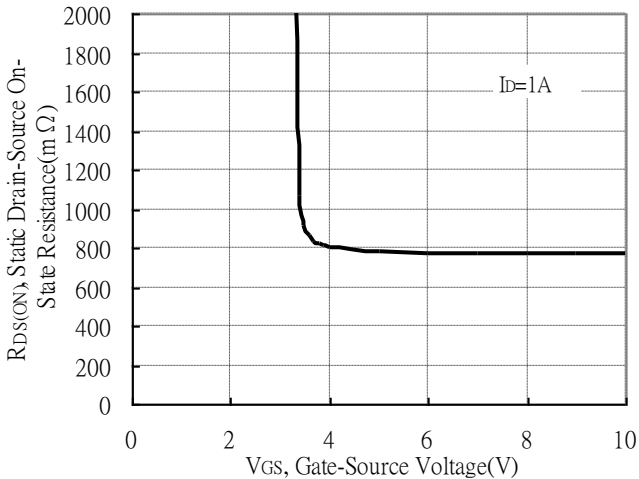
Static Drain-Source On-State resistance vs Drain Current



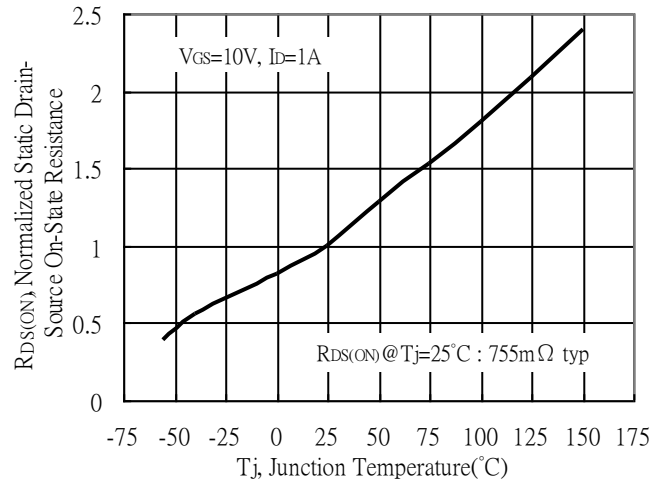
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

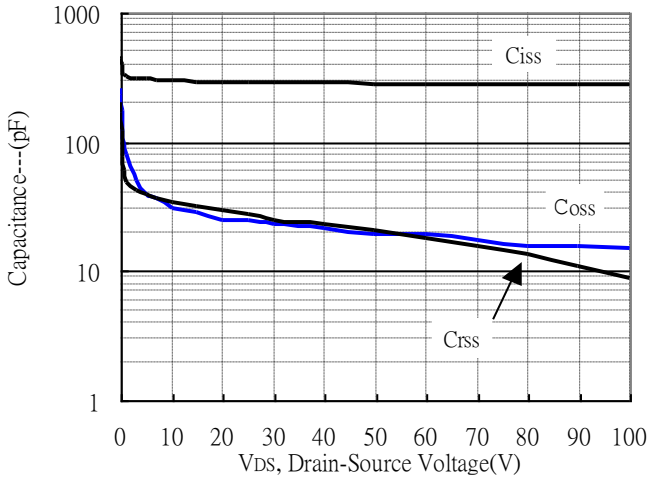


Drain-Source On-State Resistance vs Junction Temperature

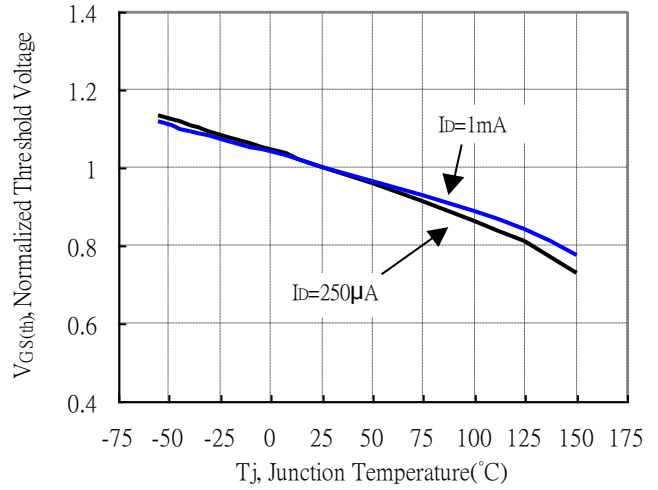


Typical Characteristics(Cont.)

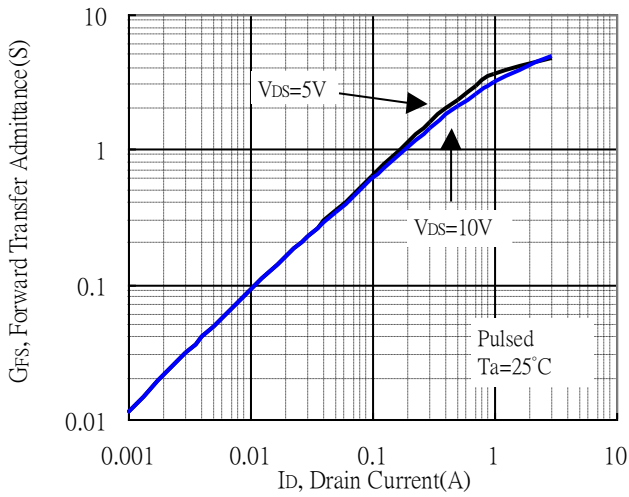
Capacitance vs Drain-to-Source Voltage



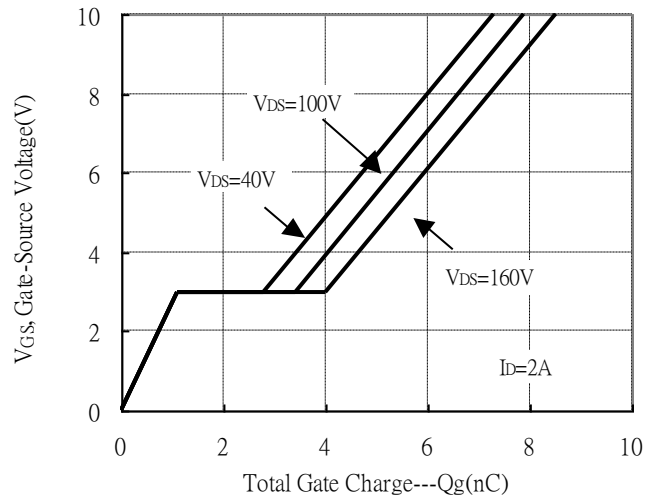
Normalized Threshold Voltage vs Junction Temperature



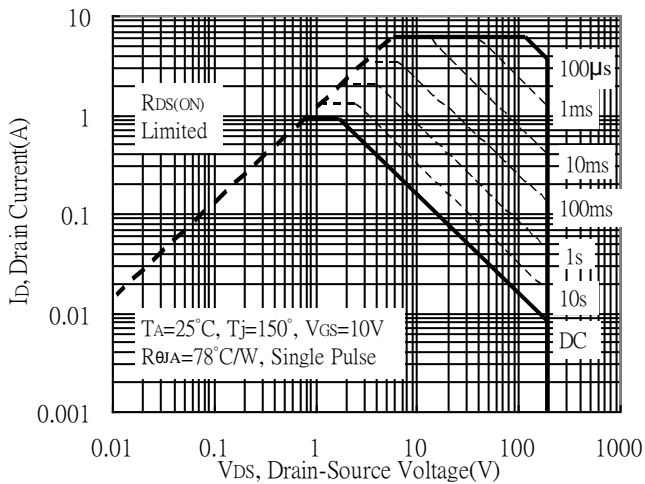
Forward Transfer Admittance vs Drain Current



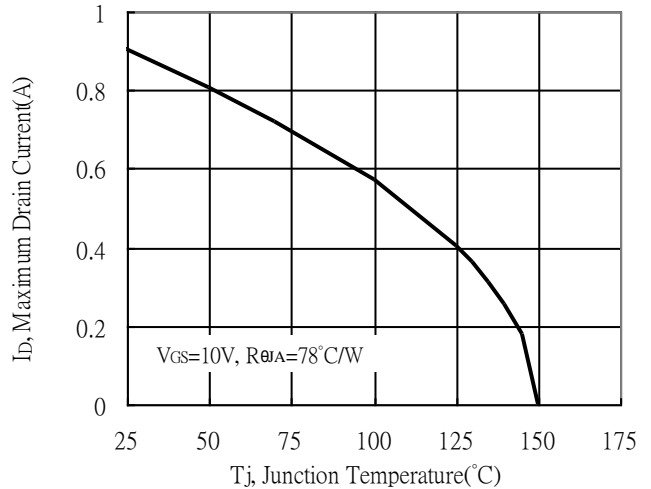
Gate Charge Characteristics



Maximum Safe Operating Area

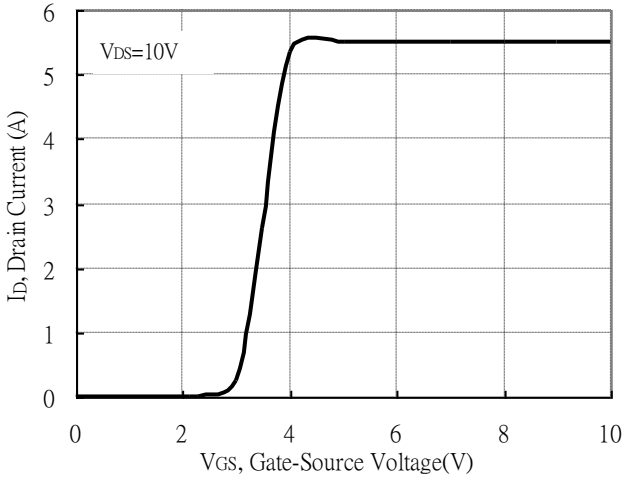


Maximum Drain Current vs Junction Temperature

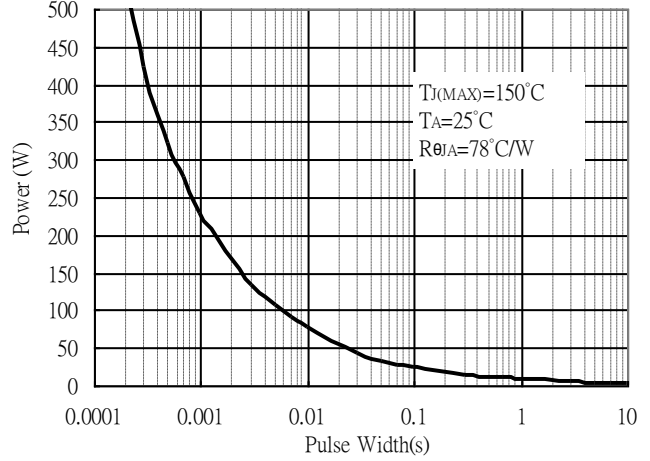


Typical Characteristics(Cont.)

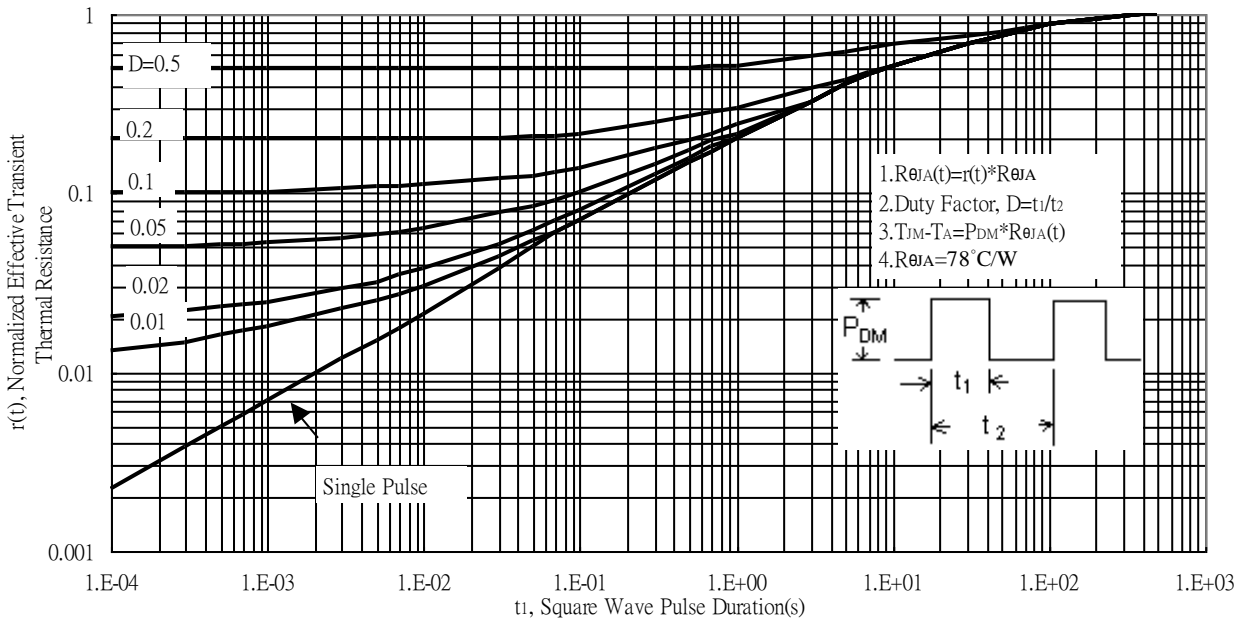
Typical Transfer Characteristics



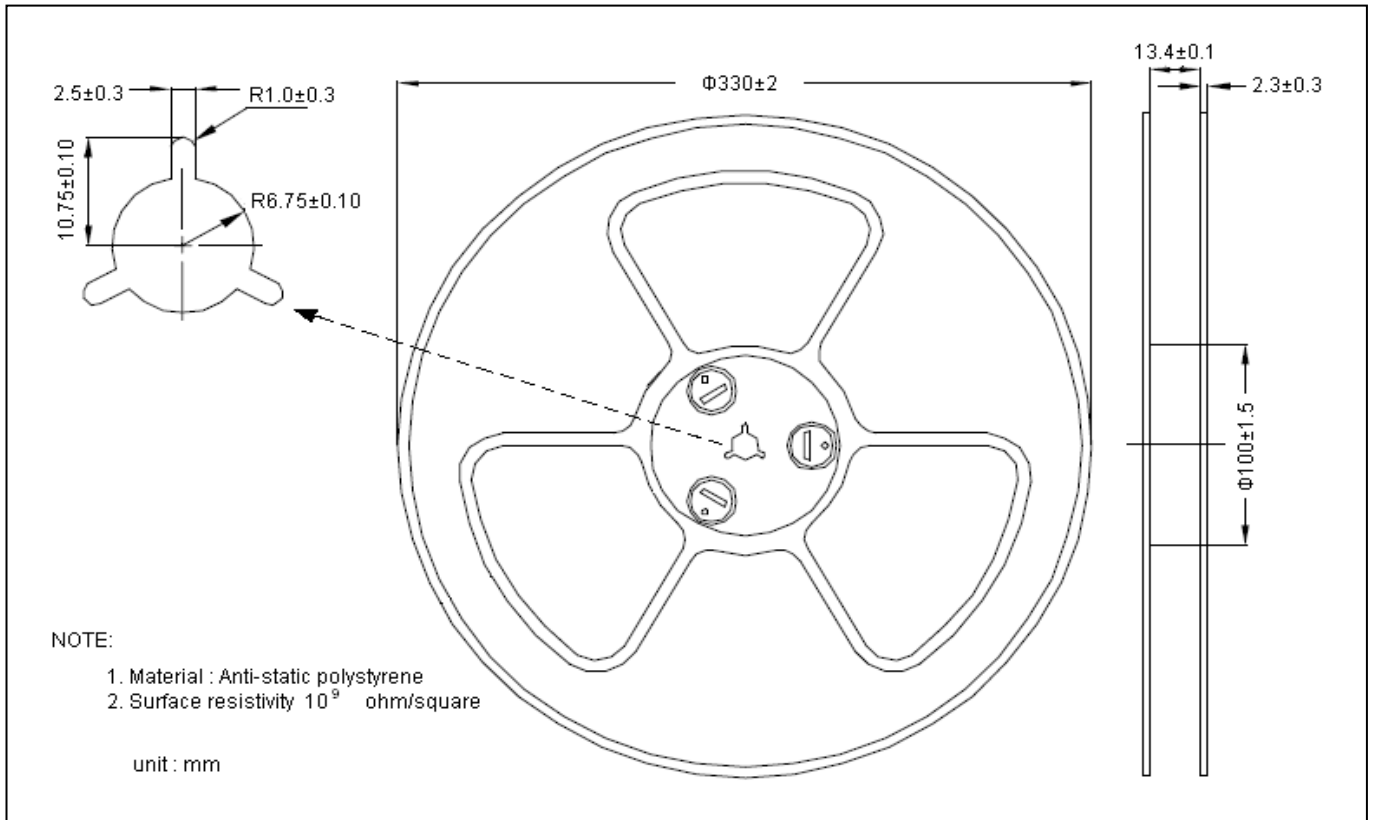
Single Pulse Maximum Power Dissipation
 (Please see Note on page 2)



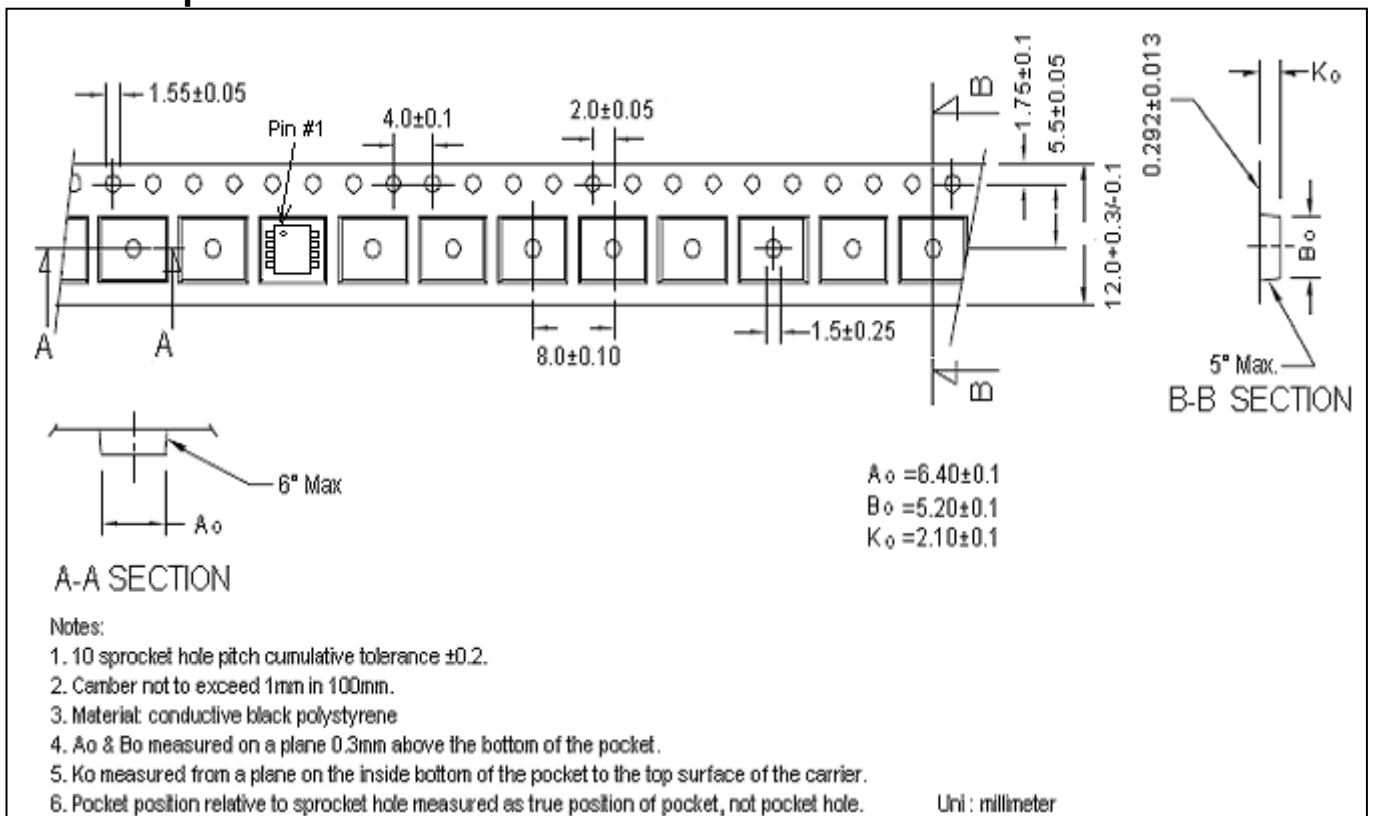
Transient Thermal Response Curves



Reel Dimension



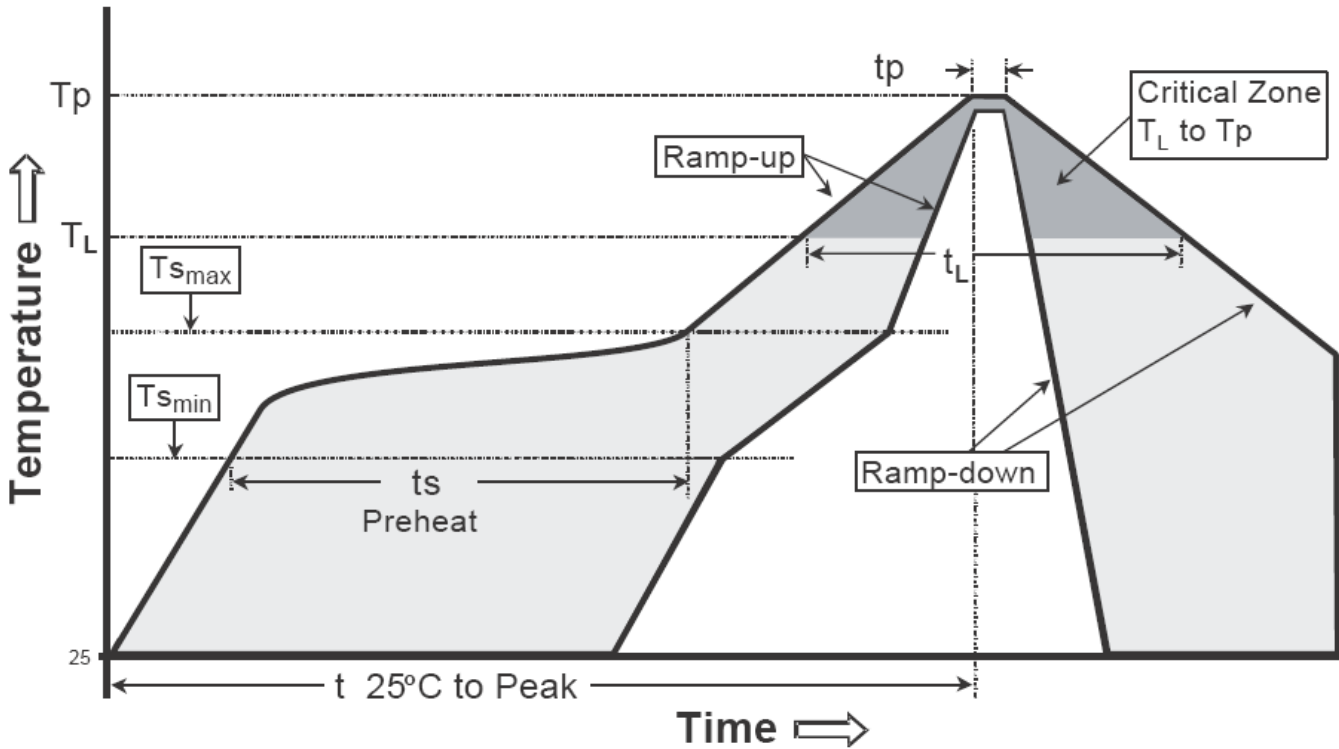
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

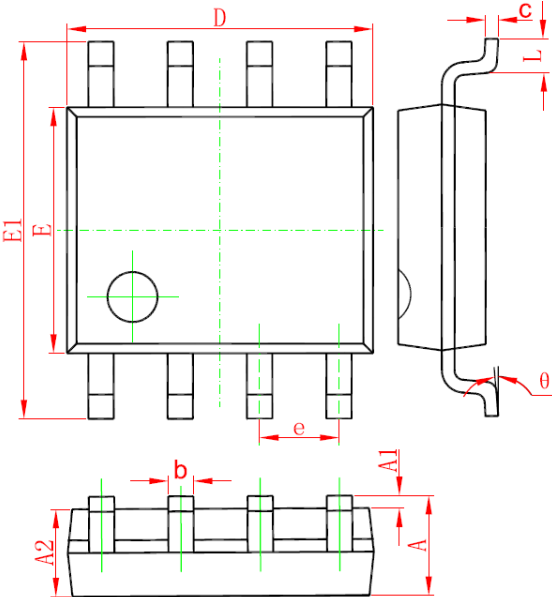
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Ts_max to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts_min)	100°C	150°C
-Temperature Max(Ts_max)	150°C	200°C
-Time(ts_min to ts_max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T_L)	183°C	217°C
- Time (t_L)	60-150 seconds	60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

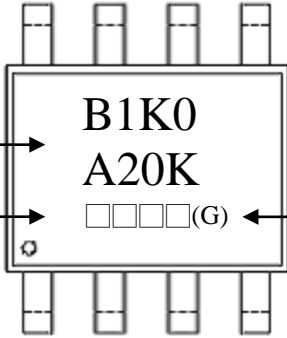
Note :1. All temperatures refer to topside of the package, measured on the package body surface.
 2.For devices mounted on FR-4 PCB of 1.6mm or equivalent grade PCB. If other grade PCB is used, care should be taken to match the coefficients of thermal expansion between components and PCB. If they are not matched well, the solder joints may crack or the bodies of the parts may crack or shatter as the assembly cools.

SOP-8 Dimension



The diagram shows three views of an 8-lead SOP-8 package: a top view with dimensions D, E, E1, and e; a side view with dimensions L, c, and θ ; and a bottom view with dimensions A, A1, A2, and b.

Marking:



The marking diagram shows a top view of the package with the following markings: "B1K0" and "A20K" in the center, a date code "□□□□(G)" below them, and a production site code "□" to the right. Arrows point from the labels "Device Code", "Date Code", and "Production site code" to their respective markings.

Date Code(counting from left to right) :

1st code: year code, the last digit of Christian year
 2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D
 May→E, Jun→F, Jul→G, Aug→H, Sep→J,
 Oct→K, Nov→L, Dec→M
 3rd and 4th codes : production serial number, 01~99

Production site code : blank→ JCET, G →GEM

8-Lead SOP-8 Plastic Package
 CYStek Package Code: Q8

*: Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069	E	3.800	4.000	0.150	0.157
A1	0.100	0.250	0.004	0.010	E1	5.800	6.200	0.228	0.244
A2	1.350	1.550	0.053	0.061	e	*1.270		*0.050	
b	0.330	0.510	0.013	0.020	L	0.400	1.270	0.016	0.050
c	0.170	0.250	0.006	0.010	θ	0°	8°	0°	8°
D	4.700	5.100	0.185	0.200					

- Notes:** 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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